DOCUMENT CHANGE REQUEST

DCR number 707
Changes required for: N/A
Originator: Geraldine Chaumont
Date: 2012/09/03
Date sent: 2012/02/10
Organisation: STMicroelectronics
Status: IMPLEMENTED

Title:	Transistors Low Power NPN, based on type 2N2222A		
Number:	5201/002	Issue:	4

Other documents affected:

5201/004-4, 5202/001-6

Page:

5201/002: pages 6 & 16 - 5201/004: pages 5 & 13 - 5202/001: pages 5, 12 & 15

Paragraph:

5201/002: § 1.4.2, 2.9 & 2.10 - 5201/004: § 1.4.2, 2.9 & 2.10 - 5202/001: § 1.4.2, 2.4.1, 2.10 & 2.11

Original wording:

No irradiation data included in the detail specifications.

Proposed wording:

Insertion of new variants with radiation level + Insertion of Total dose radiation testing and Neutron testing paragraphs + Correction of a type error in the 5202/001.

Justification:

The customers are asking for a radiation level on bipolar transistors. At this time no radiation guarantee is included in the detail spec.

Attachments:

dcr707_attachment_final_version.docx, null

Modifications:

Modifications:
Replace the original DCR proposed wording by the following:

Addition of total dose radiation testing requirements for all Variants, to radiation level R 100kRAD(Si)

See final attachment for details of the changes & addition made to :
ESCC 5201/002 issue 4: Page 5, Para 1.4.1 & 1.4.2; Page 16, add new Para 2.9.
ESCC 5201/004 issue 4: Page 5, Para 1.4.1 & 1.4.2; Page 13, add new Para 2.9.
ESCC 5252/001 issue 6: Page 5, Para 1.4.1 & 1.4.2; Page 15, add new Para 2.10.

Approval signature:

Date signed:
2012-09-03